



FEATURES

- Ultrafast recovery time
- Low forward voltage drop
- Low leakage current
- 175 °C operating junction temperature
- Designed and qualified for industrial level

DESCRIPTION/APPLICATIONS

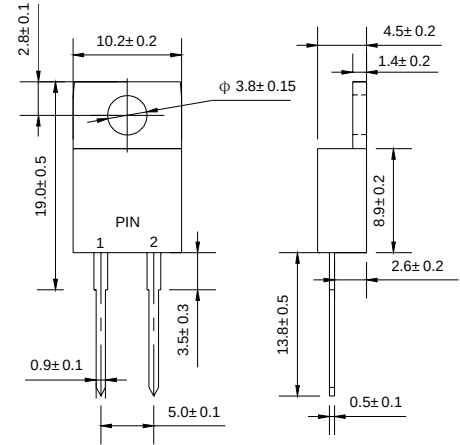
MUR.. series are the state of the art ultrafast recovery rectifiers specifically designed with optimized performance of forward voltage drop and ultrafast recovery time.

The planar structure and the platinum doped life time control, guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in the output rectification stage of SMPS, UPS, dc-to-dc converters as well as freewheeling diode in low voltage inverters and chopper motor drives.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

TO-220AC



Dimensions in millimeters

ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS
Peak repetitive reverse voltage	V_{RRM}		200	V
Average rectified forward current	$I_{F(AV)}$	Total device, rated V_R , $T_C = 150\text{ }^{\circ}\text{C}$	15	A
Non-repetitive peak surge current	I_{FSM}		200	
Peak repetitive forward current	I_{FM}	Rated V_R , square wave, 20 kHz, $T_C = 150\text{ }^{\circ}\text{C}$	30	
Operating junction and storage temperatures	T_J, T_{Stg}		- 65 to 175	$^{\circ}\text{C}$

ELECTRICAL SPECIFICATIONS ($T_J = 25\text{ }^{\circ}\text{C}$ unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Breakdown voltage, blocking voltage	V_{BR}, V_R	$I_R = 100\text{ }\mu\text{A}$	200	-	-	V
Forward voltage	V_F	$I_F = 15\text{ A}$	-	-	1.05	
		$I_F = 15\text{ A}, T_J = 150\text{ }^{\circ}\text{C}$	-	-	0.85	
Reverse leakage current	I_R	$V_R = V_R$ rated	-	-	10	μA
		$T_J = 150\text{ }^{\circ}\text{C}, V_R = V_R$ rated	-	-	500	
Junction capacitance	C_T	$V_R = 200\text{ V}$	-	55	-	pF
Series inductance	L_S	Measured lead to lead 5 mm from package body	-	8.0	-	nH

DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
Reverse recovery time	t _{rr}	I _F = 1.0 A, dI _F /dt = 50 A/μs, V _R = 30 V		-	-	35	ns
		T _J = 25 °C		-	22	-	
		T _J = 125 °C		-	39	-	
Peak recovery current	I _{RRM}	T _J = 25 °C		-	1.6	-	A
		T _J = 125 °C		-	4.1	-	
Reverse recovery charge	Q _{rr}	T _J = 25 °C		-	19	-	nC
		T _J = 125 °C		-	90	-	

THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Maximum junction and storage temperature range	T_J, T_{Stg}		- 65	-	175	$^{\circ}\text{C}$
Thermal resistance, junction to case	R_{thJC}		-	-	1.5	$^{\circ}\text{C}/\text{W}$
Thermal resistance, junction to ambient	R_{thJA}		-	-	50	
Thermal resistance, case to heatsink	R_{thCS}	Mounting surface, flat, smooth and greased	-	0.5	-	
Weight			-	2.0	-	g
			-	0.07	-	oz.
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)
Marking device		Case style TO-220AC	MUR1520			

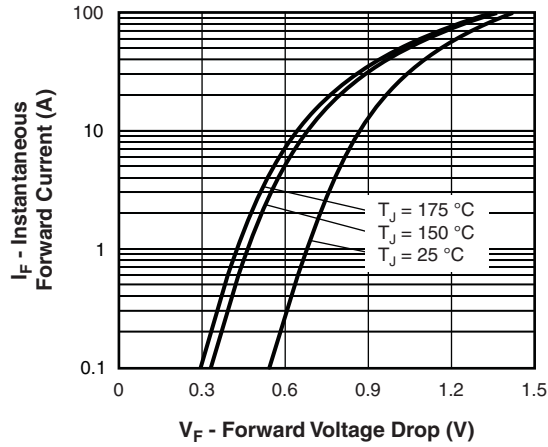


Fig. 1 - Typical Forward Voltage Drop Characteristics

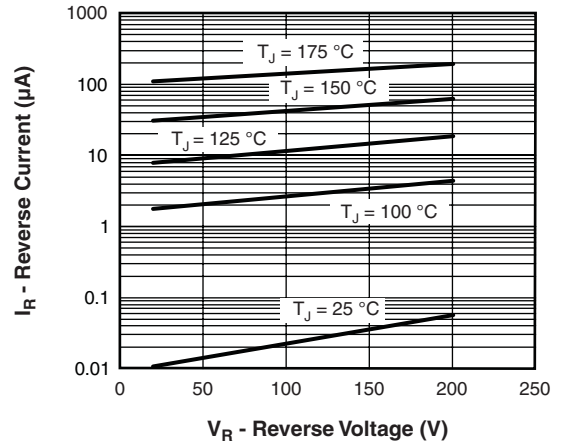


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

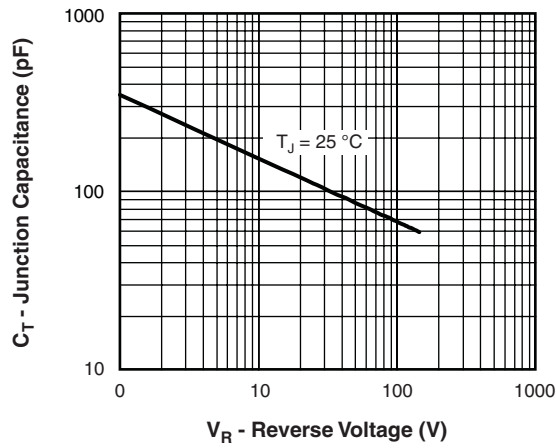


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

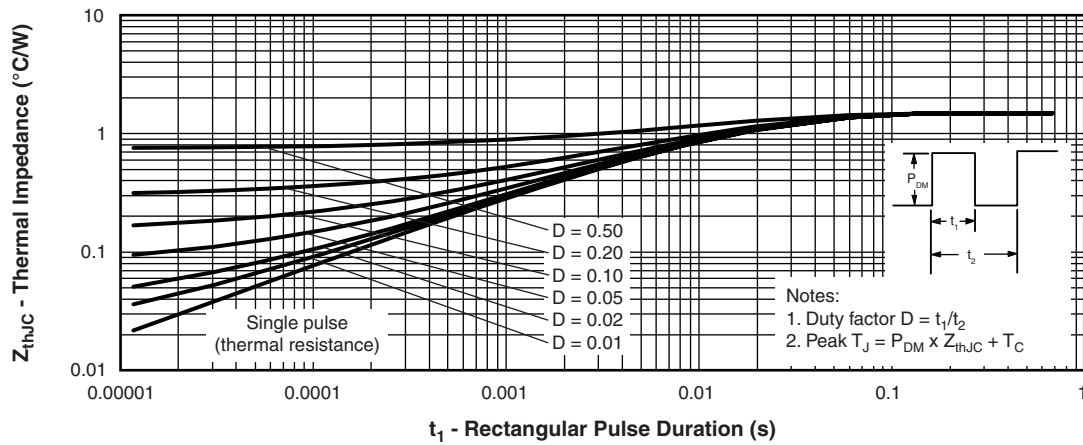


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics

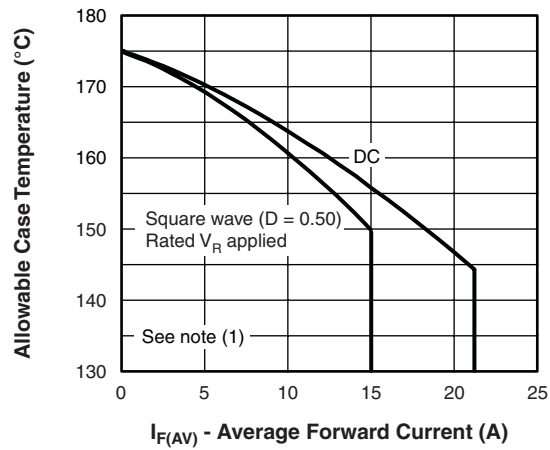


Fig. 5 - Maximum Allowable Case Temperature vs. Average Forward Current

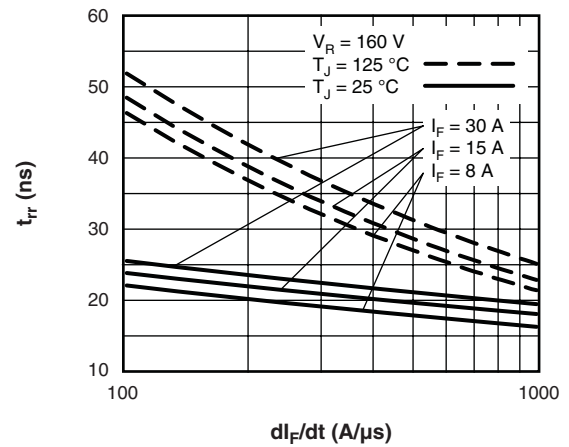


Fig. 7 - Typical Reverse Recovery Time vs. dI_F/dt

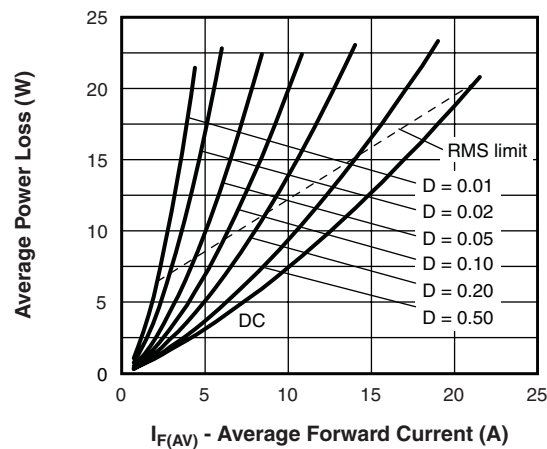


Fig. 6 - Forward Power Loss Characteristics

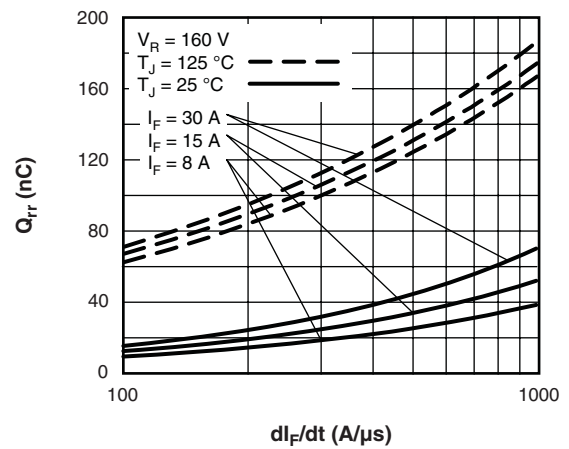


Fig. 8 - Typical Stored Charge vs. dI_F/dt

Note

- (1) Formula used: $T_C = T_J - (P_d + P_{d_{REV}}) \times R_{thJC}$;
 P_d = Forward power loss = $I_{F(AV)} \times V_{FM}$ at $(I_{F(AV)}/D)$ (see fig. 6);
 $P_{d_{REV}}$ = Inverse power loss = $V_{R1} \times I_R (1 - D)$; I_R at V_{R1} = Rated V_R